

Sixth Semester B.E. Degree Examination, July/August 2022
Microelectronics Circuits

Time: 3 hrs

Max. Marks: 100

Note: Answer any FIVE full questions, selecting atleast THREE questions from Part-A and any TWO questions from Part-B.

PART - A

- 1 a. Mention the voltage requirements of an enhancement NMOSFET to work in different regions of operation. Derive an expression for current I_{ds} in linear region of operation with necessary diagrams. (10 Marks)
- b. Design the circuit of Fig.Q1(b) so that the FET operates at $I_{ds} = 0.4 \text{ mA}$ and $V_d = 0.5 \text{ V}$. The NMOSFET has $V_{tn} = 0.7 \text{ V}$, $\mu_n C_{ox} = 100 \mu\text{A/V}^2$, $L = 1 \mu\text{m}$, $W = 32 \mu\text{m}$ and $V_{DD} = 2.5 \text{ V}$.

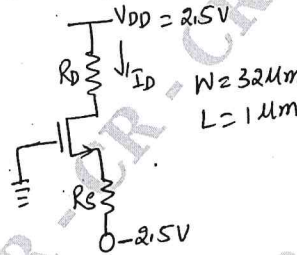


Fig.Q1(b)

(10 Marks)

- 2 a. Explain the graphical derivation of CS MOSFET amplifier transfer characteristics with suitable diagrams. (10 Marks)
- b. Explain the working of single stage common gate MOSFET amplifier circuit. Define R_{in} , V_o , A_{V_o} , A_V and G_V for the same circuit. (10 Marks)
- 3 a. Compare NMOSFET and BJT with respect to the following parameters:
 - (i) Active region voltage values
 - (ii) Current expression in the active region
 - (iii) Low frequency T-model
 - (iv) Transconductance g_m
 (08 Marks)
- b. Explain with suitable diagram current mirror and current steering circuits. (08 Marks)
- c. Explain briefly cascade amplifiers. (04 Marks)
- 4 a. Design the current of Fig.Q2(a) to obtain an output current whose nominal value is $100 \mu\text{A}$. Find R if Q_1 and Q_2 are matched and have channel lengths of $1 \mu\text{m}$, channel widths of $10 \mu\text{m}$, $V_t = 0.7 \text{ V}$ and $k'_n = 200 \mu\text{A/V}^2$, what is the lowest possible value of V_0 ? Assume $V'_A = 20 \text{ V}/\mu\text{m}$. Find the out resistance of the current source. Also find the change in output current resulting from a $+1 \text{ V}$ change in V_0 .

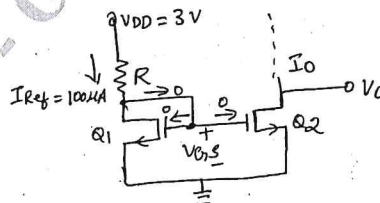


Fig.Q2(a)

(10 Marks)

- b. Explain the working of CMOS implementation of common source amplifier and define the voltage gain. (10 Marks)

- 5 a. Explain the operation of BJT differential pair configuration. (10 Marks)
 b. Explain the frequency response of current mirror loaded MOS differential pair circuit. (10 Marks)

PART – B

- 6 a. Explain how noise reduction and band-width extension can be achieved using negative feedback with necessary diagrams and expressions. (10 Marks)
 b. Explain the ideal structure of a series-series feedback amplifier with figures and expressions. (10 Marks)
- 7 a. Design an inverting op-amp circuit to form the weighted sum V_0 of two inputs V_1 and V_2 . It is required that $V_0 = -(V_1 + 5V_2)$. Select values for R_1 , R_2 and R_f so that for a maximum o/p voltage of 10V, the current in the f/b resistor will not exceed 1 mA. (06 Marks)
 b. Explain different amplifiers with neat diagrams. (08 Marks)
 c. Explain briefly Sample and Hold circuits. (06 Marks)
- 8 a. Explain the following characteristics of a logic family. (06 Marks)
 b. Write about the dynamic operation of CMOS inverter with necessary diagrams and expressions. (10 Marks)
 c. Draw the CMOS schematic and AOI implementation for

$$Y = \overline{AB + CD}$$
 (04 Marks)

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